

Technical Data  
Data Sheet 4949, Rev. -

## SILICON SCHOTTKY RECTIFIER DIE Extremely Low Forward Voltage Drop

### Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

### Features:

- Soft Reverse Recovery at Low and High Temperature
- Extremely Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

### Maximum Ratings<sup>(1)</sup>:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	45	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form	60	A
Max. Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3 ms, Sine pulse <sup>(1)</sup>	860	A
Max. Junction Temperature	$T_J$	-	-65 to +125	°C
Max. Storage Temperature	$T_{stg}$	-	-65 to +175	°C

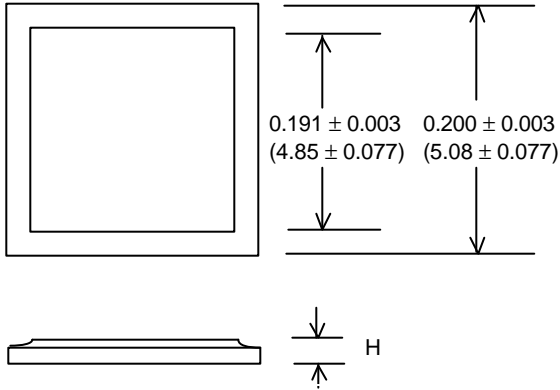
### Electrical Characteristics<sup>(1)</sup>:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	@ 60A, Pulse, $T_J = 25\text{ °C}$	0.54	V
	$V_{F2}$	@ 60A, Pulse, $T_J = 125\text{ °C}$	0.50	V
Max. Reverse Current	$I_{R1}$	@ $V_R = 45V$ , Pulse, $T_J = 25\text{ °C}$	5.0	mA
	$I_{R2}$	@ $V_R = 45V$ , Pulse, $T_J = 125\text{ °C}$	800	mA
Max. Junction Capacitance	$C_T$	@ $V_R = 5V$ , $T_C = 25\text{ °C}$ $f_{SIG} = 1MHz$ , $V_{SIG} = 50mV$ (p-p)	2600	pF

(1) in SHD package

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**Mechanical Dimensions: In Inches / mm**



Bottom side metalization Ag - 30 kÅ minimum.

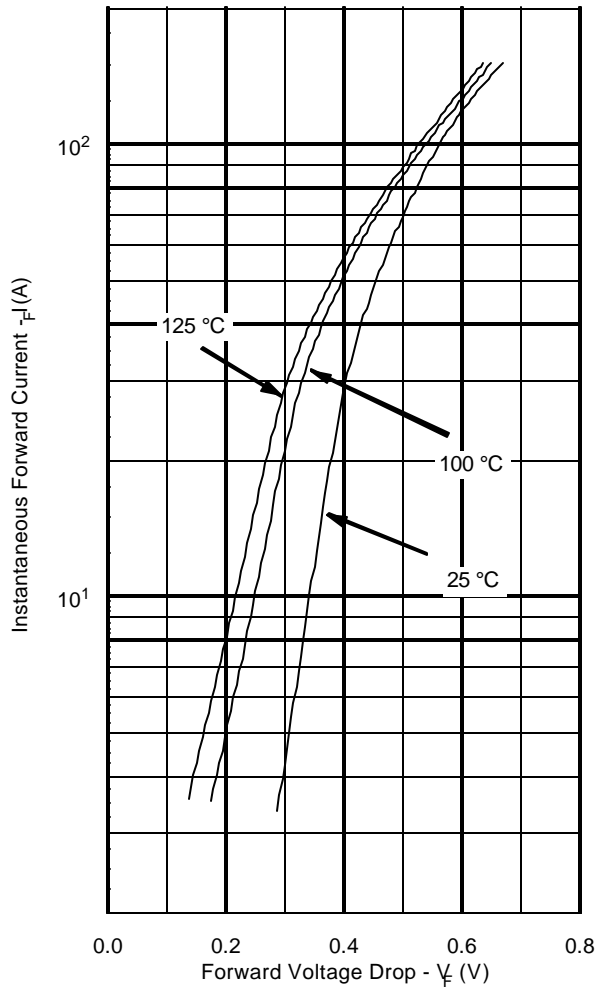
Top side metalization Al - 25 kÅ minimum  
or Ag - 30 kÅ minimum.

Bottom side is cathode, top side is anode.

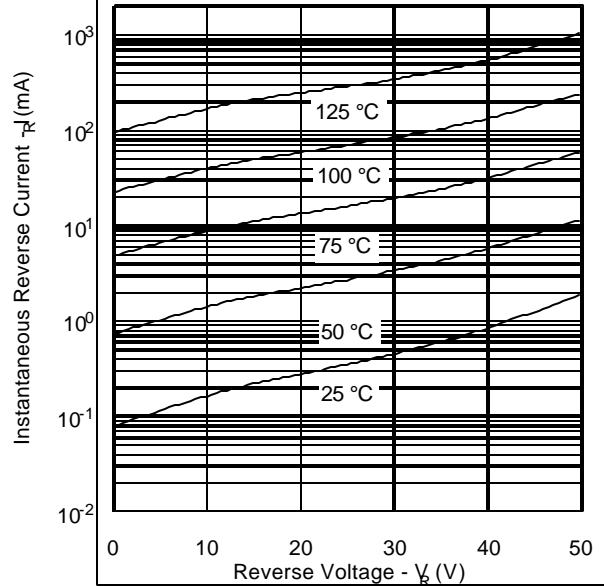
Dimension H = 0.0105 ± 0.001 (0.27 ± 0.026) for Al top;

Dimension H = 0.0155 ± 0.001 (0.39 ± 0.026) for Ag top.

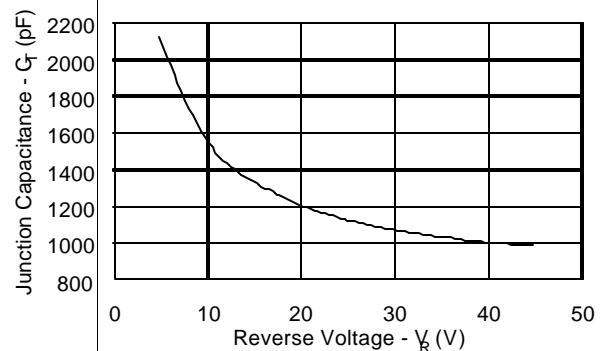
**Typical Forward Characteristics**



**Typical Reverse Characteristics**



**Typical Junction Capacitance**



**TECHNICAL DATA**

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